

JC973 U.S. PTO
 09/974808
 10/12/01

November 23, 1998

III. FEES

This Information Disclosure Statement is being filed concurrent with the filing of a continuation-in-part, continuation, or divisional patent application; therefore, no fee is required.

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Respectfully submitted,

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Enclosures: ☒ PTO-1449
☐ References
☐ Foreign Search Report
☐ Other:

(Rev. 04/19/2000)

Form PTO-1449

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

ATTY DOCKET NO.
PF-2200DIV

APPLICATION NO.
NEW

APPLICANT
Yoshiaki YAMADA et al.

FILING DATE
October 12, 2001

GROUP	UNASSIGNED
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JC9730 US. PTO
10/12/01

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER							DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	6	0	7	7	7	8	2	2000-06-01	Hsu et al.			
	6	0	5	9	8	7	2	2000-05-01	Ngan et al.			
	6	0	4	6	1	0	0	2000-04-01	Ramaswami et al.			
	5	9	8	5	7	5	6	1999-11-01	Shinmura			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
												YES	NO
	1	9	3	1	1	7		1989-04	JAPAN				
	4	1	9	6	4	8	6	1992-07	JAPAN				
	7	1	6	1	6	6	2	1995-06	JAPAN				
	7	2	4	5	3	0	0	1995-09	JAPAN				
	7	7	8	7	8	9		1995-03	JAPAN				
	8	7	8	5	2	0		1996-03	JAPAN				
	8	1	8	1	2	1	2	1996-07	JAPAN				
	9	2	2	8	0	4	2	1997-09	JAPAN				
	10	6	5	0	0	4		1998-03	JAPAN				
	63	1	1	1	6	6	5	1988-05	JAPAN				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

	J.P. Seidel, et al. "Integrated deposition of TiN barrier layers in cluster tools", Proc. of the SPIE, Vol. 1549, pp. 30-40. (abstract)
	H.J. Barth, et al. "TEM analysis of the spiking mechanism in Al-filled contacts", Advanced Metallization and Interconnect Systems for ULSI Applications in 1996", pp. 305-311. (abstract)
	D.H. Lee, et al. "Characteristics of CMOSFETs with sputter-deposited W/TiN stack gate" 1995 Symp. on VLSI Tech. Digest of tech. Papers, IEEE and JSAP pp. 119-120.
	S.-L. Zhang, et al. "Influence of hydrogen on chemical vapor deposited W on sputter-deposited TiN" Applied Physics Lett., Vol. 67, No. 20, pp. 2998-3000.
	J. van Gogh et al.. "Characterization of improved TiN films by controlled divergence sputtering, pp. 310-313, ISMIG, Vol. 101, No. 92, VMIC Conference, June 9-10, 1992.
	A. Mouroux, et al. "Impact of rapid thermal annealing of Ti-TiN bilayers on subsequent chemical vapor deposition", Advanced Metallization for Future ULSI. Symp., pp. 365-370. (abstract)

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.